

Selected Publications: Si-Ge HMOS Project Theory and Modelling

Si/SiGe Heterostructure Parameters for Device Simulations

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Semiconductor Science and Technology 19,1174-1182, (2004)

Reduced interface roughness in sub-100nm strained Si n-MOSFETs - A Monte Carlo simulation study,

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The impact of interface roughness scattering and degeneracy in relaxed and strained Si n-channel MOSFETs

J. R. Watling, L. Yang, M. Borici, R. C. W. Wilkins, A. Asenov, J. R. Barker and S. Roy. Solid State Electronics 48, 1337-1346 (2004) (invited)

Impact of device geometry and doping strategy on linearity and RF performance in Si/SiGe MODFETs

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Green Function Simulation Study of Non Self-Averaging Scattering Processes in
Atomistic Semiconductor Devices
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L. YANG, J.R. WATLING, M. BORICI, R.C.W. WILKINS, A. ASENOV, J.R.
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Scaling Study of Si/SiGe MOSFETS for RF applications

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